

AMENDMENTS THE SPECIFICATIONS

Please replace the first paragraph on page 9 with the following amended paragraph.

Still referring to Fig. 1, a first wide-band-gap insulating layer 14, such as  $\text{SiO}_2$  or  $\text{Al}_2\text{O}_3$ , is deposited directly on the bottom electrodes 12.  $\text{SiO}_2$  insulating layer 14 can be deposited, for example, by chemical-vapor deposition (CVD) using a reactant gas such as tetraethosiloxane (TEOS). The  $\text{SiO}_2$  and  $\text{Al}_2\text{O}_3$  have band-gap widths that are greater than 8.0 eV, as shown in Table I on page 5254 in the Journal of Applied Physics, Vol. 89, No. 10, May 15, 2001. The  $\text{SiO}_2$  layer 14 can be deposited to a preferred thickness of between about 10 and 50 Angstroms. Alternatively, insulating layer 14 can be  $\text{Al}_2\text{O}_3$ , deposited, for example, by CVD or atomic layer CVD (ALCVD) techniques to a preferred thickness of between about 10 and 50 Angstroms.